

Sir:

Transmitted herewith for filing is the Patent Application of:

Inventor: SIK ON KONG, RAJAN RAJGOPAL AND GEORGE WONG

PHOTOLITHOGRAPHIC METHODS FOR MAKING LIQUID-CRYSTAL-ON-SILICON DISPLAYS WITH
ALIGNMENT POSTS AND OPTICAL INTERFERENCE LAYERS

Enclosed are:

- ☒ 8 sheets of drawing(s) - formal.
- ☒ An assignment of the invention to Chartered Semiconductor Manufacturing Ltd.
- ☐ An associate power of attorney

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TOTAL CLAIMS	36 -20=	16	x 18 =	\$ 288.
INDEP CLAIMS	5 -3=	2	x 78 =	\$ 156.
MULTIPLE DEPENDENT CLAIM PRESENTED			+ 260 =	
			SUB TOTAL	\$ 1,204.
			ASSIGNMENT	\$40.
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Respectfully submitted,

STEPHEN B. ACKERMAN, REG. NO. 37,761

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09/262000



PHOTOLITHOGRAPHIC METHODS FOR MAKING LIQUID-CRYSTAL-
ON-SILICON DISPLAYS WITH ALIGNMENT POSTS AND OPTICAL
INTERFERENCE LAYERS

This is related to Patent Application Serial No. _____
by Su Yong Jie, Ravi Sankav and Han Zhi Ciang filed as
_____ (CS 98-077) and to Serial No. _____ by Sudipto
R. Roy filed as _____ (CS 98-078), all of Chartered
Semiconductor Manufacturing LTD of Singapore Technologies.

BACKGROUND OF THE INVENTION

(1) Field of the Invention

This invention relates to new methods of
photolithographic fabrication of alignment posts and optical
interference layers directly on liquid-crystal-on-silicon
displays.

(2) Description of the Prior Art

The picture quality of liquid crystal displays from the
simple seven segments to millions of pixels is determined by
the structure used to control the variation of thickness and
position leads after wafer processing. There are known
processes for creating insulated alignment posts based on
preformed glass micro-spheres and rods; relatively low
series resistance posts can be obtained by means of
selective deposition of polysilicon and metallic silicide.

(The making of metallic vias and contacts is a comparatively well known processing art.)

US Patent 5,498,925 to Bell et al describes the formation of posts in flat panel displays using processes based on a heat-treated slurry or paste upon a glass plate. US Patent 5,597,736 teaches the function of a light-blocking layer deposited upon a semiconductor substrate material that can emit light. US Patent 5,744,824 and US 5,748,828 show various LCD structures and external optics.

Until now, it has been difficult to construct alignment posts using photolithography and also add optical interference layers simultaneously onto a semiconductor substrate material used to control the gray-level of each pixel.

BRIEF SUMMARY OF THE INVENTION

A principal object of the present invention is to describe various new methods for building a flat-panel liquid-crystal display upon an integrated circuit (IC) die with inter-related alignment between the posts supporting the overlaying glass cover plate and optical interference layers employed to improve image quality.

Another object of this invention is to describe effective and very manufacturable methods of photolithographic formation of insulating alignment posts (also called studs or pillars). These methods can be used in processing many different device types, and are described in this application for liquid crystal display devices as a way of illustrating their embodiment at a pixel density beyond that achievable with preformed micro-glass spheres and rods.

A further object of the present invention is to describe methods of deposition for both the posts and the optical interference layers that are independent of each other and retain their desired feature during deposition of subsequent features. The various methods are classified into five method categories: 1) silicon oxide wet etching; 2) amorphous silicon plasma etching; and 3) nitride plug filling; 4) insulating material lift-off; 5) photosensitive polyimides.

Five new methods for the formation of an improved liquid-crystal-on-silicon display are described, in which the device structure is enhanced by the photolithographic building of alignment posts among the mirror pixels of the micro-display. At the same time these five methods accommodate the fabrication of an optical interference

multilayer that improves the image quality of the reflected light. These five methods are:

Silicon Dioxide Posts by Wet Etching - wherein said alignment posts are formed by the process of silicon dioxide wet etching upon the said silicon substrate.

Amorphous Silicon Posts by Plasma Etching - wherein said alignment posts are formed by the process of amorphous silicon plasma etching upon the said silicon substrate.

Silicon Nitride Posts by Plug Filling.- wherein said alignment posts are formed by the process of silicon nitride plug filling upon the silicon substrate.

Insulation Material Posts by Lift-Off - wherein said alignment posts are formed by the process of insulation material lift-off upon the said optical interference layer OIL.

Polyimide Posts by Photosensitive Etching - wherein said alignment posts are formed by the process of polyimide photosensitive etching upon the OIL.

BRIEF DESCRIPTION OF THE DRAWINGS

In the accompanying drawings forming a material part of this description, there is shown:

Figs. 1 through 3 schematically illustrate in cross-sectional representation a preferred embodiment of the device structure of the present invention. The base silicon substrate with the formed metallic pixels on the display device is shown in Fig. 4.

The process flow for making the alignment posts and the optical interference layers by the five process categories is shown in Figs. 5 to 19.

Fig. 5 shows a detailed cross-sectional diagram of the device ready to be covered with the optical interference layers.

Fig. 6 shows the optical interface layers deposition.

Fig. 7 shows the thick silicon oxide layer deposit on top of the OIL.

Fig. 8 shows the photomask after etch off of the excess silicon oxide with wet etch.

Fig. 9 shows the thick amorphous silicon deposition on top of the OIL.

Fig. 10 shows the result of post photomasking and plasma amorphous silicon etching.

Fig. 11 shows the thick oxide layer deposition of top of the OIL used in forming the plugs of silicon nitride.

Fig. 12 shows the result of post photomasking, plasma oxide etching and plasma enhanced nitride chemical vapor deposition.

Fig. 13 shows the result of silicon nitride etch-back with plasma and oxide removal with wet etching.

Fig. 14 shows the result of the deposition consequence of a thick photoresist, SiO by thermal evaporation, and a thin resist layer prior to the deposition of the insulation material posts.

Fig. 15 shows the result of the photomasking, plasma etching the SiO layer and another plasma etch of the bottom resist prior to the deposition of the insulation material.

Fig. 16 shows the cross-section after the thermal or electron beam evaporation of insulation material.

Fig. 17 shows the cross-section after the photoresist lift-off in an ultrasonic bath of resist remover.

Fig. 18 shows the cross-section after the photosensitive polyimide is deposited.

Fig. 19 shows the cross-section after the post photomasking and development of the photosensitive polyimide.

Fig. 20 schematically illustrates in cross-sectional representation one type of final embodiment of this invention for this liquid-crystal-on-silicon display device.

Fig. 21a and Fig. 21b illustrate (by means of a top view) how the display device can be constructed with the alignment posts between the pixels.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

Referring now more particularly to Fig. 1, here is shown a portion of a partially completed integrated circuit liquid-crystal display. The glass cover plate 10 provides the transparent enclosure for the external incident light to be reflected back to an observer. The strength of reflected light is dependent on the light polarization, absorption and

light scattering properties of each liquid-crystal display pixel, which is controlled by the electrical field established within the liquid crystal material 11. The IC die 12, separated from the glass plate by the alignment posts 14 generates these E-fields. The resultant space between the glass plate and the silicon wafer is filled with the chosen liquid crystal material. Light, either provided or ambient, enters the open face of the liquid-crystal-on-silicon and is reflected from the underlying pixels to form a viewable pattern of polarized light, i.e. the image is viewed directly or projected through an optical polarized system.

Fig.2 illustrates the bonding pads 20 on the IC die to which the external wires 22 are attached. The silicon wafer contains the embedded control circuits that activate the pixel patterns in the viewable area 24. The optical properties of the liquid crystal (e.g. the rotation of plane-polarized light or the dispersion of light) are influenced by the electric fields above the IC surface. A small change in voltage makes a large change in the optical transmission. Because this invention teaches the photolithographic making of patterns of alignment posts, the ratio of pixels 30 to posts 14 is often fabricated in the range 1:1 to 1:10000. As shown in Fig. 3, the photolithographic method permits these alignment posts to be constructed in the space between adjacent pixels.

The process steps for making the alignment posts and optical interference layers by means of the various photolithographic categories is shown in Figures 4 to 20.

Starting with Fig. 4, the conductive metallic (or poly) layer 30 is formed over the silicon oxide 40, which is formed on top of the second metal layer 20 on the IC. Prior to formation of the silicon oxide 40, the metal 20 as bond pad is deposited on silicon dioxide layer 41. A silicon semiconductor substrate 09 is coated with an silicon dioxide insulating layer 15 and has active devices therein and an metal layer (metal 1) 16 upon which silicon dioxide layer 41 is formed. Then a photoresist layer is formed over the metal 30 to construct the pixels. The photoresist is exposed and a portion removed to provide that each pixel retains a metallic layer, which shall act as a mirror reflector for the light incident upon said pixel.

After the resist is stripped, as shown in Fig. 5, the device is ready to be covered with the optical interference layers 60. Optical interference layers are used to improve light reflections. Careful attention is required in constructing these optical interference layers so as not to disturb any underlying devices and/or posts. Fig. 6 shows the resultant structure, which is ready for the fabrication of alignment posts.

The optical interference layer coating (OIL) is composed of oxides and nitrides, coated into multiple layers of insulating material with properties of varying optical indices of refraction. The alignment posts are constructed after the OIL is made by one of the five process methods described herein:

Method 1 - Silicon Dioxide Posts by Wet Etching

A silicon oxide layer 70, about 1 micron thick, is deposited on top of the OIL 60, as shown in Fig. 7. The photomask 80, about 4 microns across, is formed at the location of each alignment post, and a wet etch, such as hydrogen fluoride or buffered HF, is applied to remove the excess silicon oxide. The resultant alignment posts 71 are shown in Fig. 8 (in this illustration on the peripheral). After removing the alignment post photoresist, a photomask is deposited to make the metal bonding pad 20, and the said pad is etched into the OIL 60 plus silicon oxide 40, followed by the removal of this photomask and formation of the bond pads 20.

Method 2 - Amorphous Silicon Posts by Plasma Etching

An amorphous silicon layer 90, about 1 micron thick, is deposited on top of the OIL 60, as shown in Fig. 9. The

photomask 100, about 2 microns across, is formed at the location of each alignment post, and a plasma silicon etch, such as CF₄/O₂ or SF₆, is applied to remove the excess amorphous silicon. This plasma etch has a high selectivity in the presence of silicon nitride, and will not damage the silicon nitride top layer in the OIL 60. The resultant alignment posts 101 are shown in Fig. 10 (in this illustration between the pixels). This process method is completed as described in Method 1, by removing the photoresist 80 and formation of the bond pads 20.

Method 3 - Silicon Nitride Posts by Plug Filling

A silicon oxide layer 110, about 1 micron thick, is deposited on top of the OIL 60, as shown in Fig. 11. The photomask is formed over the oxide, except the location of each alignment post, and a plasma oxide etching is used to remove the silicon oxide not covered by the photomask, creating cavities 120, including some or all of the OIL at the base of the post cavity. Subsequently the post cavities 120 are filled with silicon nitride 121 deposited by plasma enhanced chemical vapor deposition (PECVD). [The plasma enhancement provides low temperature deposition (about 200 degrees centigrade) during the deposition over that obtained without the existence of the plasma. Without the plasma, the nitride deposition is in the range of 700 degrees centigrade.]

Subsequently a silicon nitride etch-back (also using a plasma etch) removes all the PECVD nitride except the cavity plugs 122. The plug filling of silicon nitride is not totally etched away by the plasma because the plasma etching is stopped after the nitride at the surface is removed. The remaining oxide 110 is removed with a wet etch, such as HF or buffered HF, as shown in Fig. 13. The wet etch does not remove the silicon nitride plugs because the selectivity between SiO₂ and the nitride is infinite for HF etching, nor the OIL top layer because it is also a nitride. This process method is completed by formation of the exposed bond pads 20, as shown previously via a top sectional view in Fig. 2, and again later in a cross-sectional view in Fig. 20.

Method 4 - Insulation Material Posts by Lift-off

A photo resist or PMMA acyclic layer 140, about two microns thick, is formed on top of the OIL, and a silicon monoxide layer 141 is placed over the photoresist 140 by thermal evaporation. These steps are followed by formation of another photoresist layer 142, about 1 micron thick, upon the silicon monoxide 141, as shown in Fig. 14. After photomasking the photoresist 142 is developed to expose the location of the plugs 150, the SiO layer 141 is etched with a CF₄ plasma and the bottom photoresist 140 is etched with an oxygen plasma, as shown in Fig 15. The cavities 150 in

the bottom thicker photoresist are then filled with insulation material 152, (calcium fluoride, silicon monoxide, yttrium oxide, aluminum oxide) by thermal or electron beam evaporation; E-beam evaporation is shown in fig. 16. The electron beam 160 is deviated by a magnetic field to strike on the material source, which is then evaporated and deposited onto the wafer. Control of the amount of the material evaporated is normally done by a crystal film thickness monitor. The bottom photoresist 140, silicon monoxide 141, and everything on top of SiO is removed by an acetone (or similar) ultrasonic bath, as shown in Fig. 17. The resist removal processing step does not affect the insulation material posts because these materials do not dissolve in acetone and stick well to the substrate. The posts made of insulation material are left among the pixels as shown, or around the peripheral as described in a prior method of this application. The process method is completed by formation of the bond pads 20.

Method 5 - Polyimide Posts by Photosensitive Etching

A photosensitive polyimide layer 180, about 1 micron thick, is formed on top of the OIL 60, as shown in Fig. 18. The photosensitive polyimide is deposited by spinning. This layer 180 is exposed to an UV light pattern so as to develop the polyimide to be used as the alignment post material. The unexposed photosensitive polyimide is then removed by

development, as shown in Fig. 19, leaving the polyimide posts 191. This process method is completed by the formation of the bond pads 20.

To complete the IC packaging, the IC is mounted onto a lead film and wires (22) are bonded from the legs of the lead film to the metal pad 20, as shown in Fig. 20.

The top-view of one possible display device layout, shown in Fig. 21a and Fig. 21b, illustrates the location of the alignment posts, for example 191. While this drawing shows the posts 191 to be located among the metallic pixels 30, an alternative design would have some or all the alignment posts intermixed with the bonding pads 20 on the peripheral.

For all five methods of photolithographic formation of alignment posts on LCD-on-silicon display devices, the existence of numerous alignment posts permits the usage of an ultra-thin glass plate or cover over the liquid crystal. Both the workpage of the wafer and the glass plate do not affect the thickness of the LCD material. This implementation results in lightweight displays for portable applications. Glass covers supported by alignment posts are typically 0.5 millimeters in thickness, and can range from 0.1 mm to 2 mm.

While the invention has been particularly shown and described with reference to the preferred embodiments thereof, it will be understood by those skilled in the art that various changes in form and details may be made without departing from the spirit and scope of the invention.

WHAT IS CLAIMED IS:

1. A method of forming insulating material alignment posts associated with active device structures comprising:
 providing a silicon semiconductor wafer having patterned said active device therein and thereon; and
 forming said insulating material alignment posts in a pattern over said pattern of active device structures.
2. A method according to Claim 1 wherein said optical interference layer improves the reflectivity of the said metallic mirror.
3. The method of claim 1 wherein said optical interference multilayer stack is formed by the process of plasma-enhanced chemical vapor deposition.
4. The method of claim 1 wherein said optical interference multilayer stack is composed of the materials formed by the process of plasma-enhanced chemical vapor deposition.
5. A method according to Claim 1 wherein said optical interference layer is between about 1000 Angstroms and 10000 Angstroms in total thickness.

6. A method according to Claim 1 wherein said alignment posts are placed on the said silicon wafer, realizing micro-display pixels.
7. A method according to Claim 1 for building the said alignment posts to a height from 0.3 microns to 5 microns on the resulting liquid-crystal-on-silicon micro-display.
8. A method of forming a device structure that combines insulating materials for alignment posts and optical interference layers associated with an active device structure in a silicon body comprising:
- providing a silicon semiconductor wafer having a pattern of active device structures therein and thereon;
 - forming a first metallic layer there over;
 - forming a silicon-oxide insulation layer over the said first metallic layer;
 - forming a second metallic layer over the said silicon oxide layer, which is used both for connections and for bonding pads;
 - forming a silicon dioxide insulation over the said second metal layer;
 - forming a third metallic layer thereover;
 - forming a photoresist mask over the said third metallic layer having a covering over the planned pixel

locations of the said liquid-crystal-on-silicon display device;

removing the said third metallic layer not covered by the said photoresist mask;

removing the said photoresist mask to provide that each said pixel retains said metallic layer, which shall act as a mirror reflector for the light incident upon said liquid-crystal-on-silicon display device;

depositing the said optical interference layers of silicon oxide/silicon nitride/silicon oxide/silicon nitride over said third metallic layer and said silicon oxide layer.

9. The method of claim 8 wherein said alignment posts are formed by the process of silicon dioxide by wet etching upon the said silicon substrate.
10. The method of claim 9 for forming a silicon dioxide layer of thickness between about 0.1 to 5 microns to achieve the desired height of the alignment posts.
11. The method of claim 9 for forming a photoresist mask over the said silicon oxide layer to cover the location of each planned alignment post.
12. The method of claim 9 for removing the said silicon oxide layer to form the said alignment posts with a wet

etch (such as HF or buffered HF), and removing the said photoresist mask.

13. The method of claim 8 wherein said alignment posts are formed by the process of amorphous silicon by plasma etching upon the said silicon substrate.
14. The method of claim 13 for forming an amorphous silicon layer of thickness between about 0.1 and 5 microns to achieve the desired height of the alignment posts.
15. The method of claim 13 for forming a photoresist mask over the said amorphous silicon layer to cover the location of each planned alignment post.
16. The method of claim 13 for removing the said amorphous silicon to form the said alignment posts by plasma etch, and removing the said photoresist mask.
17. The method of claim 8 wherein said alignment posts are formed by the process of silicon nitride by plug filling upon the silicon substrate.
18. The method of claim 17 for forming a PECVD oxide layer of thickness between 0.1 and 5 microns to achieve the desired height of the alignment posts.

19. The method of claim 17 for forming a photoresist mask over the said PECVD oxide layer to expose the location of each planned alignment post.
20. The method of claim 17 for forming post cavities by plasma etching of the said PECVD oxide layer.
21. The method of claim 17 for plasma enhanced chemical vapor deposition of silicon nitride into the said post cavities.
22. The method of etch-back removal of said silicon nitride, except that silicon nitride deposited in the said post cavities.
23. The method of claim 17 for removing the PECVD oxide layer by wet etch (such as HF or buffered HF) to form the said silicon nitride alignment posts, and removing the said photoresist mask.
24. The method of claim 8 wherein said alignment posts are formed by the process of insulation material by lift-off upon the said optical interference layer OIL.
25. The method of claim 24 wherein a photoresist or PMMA acyclic layer of thickness between about 1 and 5 microns is deposited upon the OIL and covered by silicon monoxide

via thermal evaporation, followed by another photoresist layer of thickness between about 0.1 and 1 micron.

26. The method of claim 24 wherein a photomask is used to form the said cavities in the said silicon monoxide by a CF₄ plasma etching of the silicon monoxide, after which the silicon monoxide serves as a mask for an oxygen plasma etching of the said two-micron bottom photoresist

27. The method of claim 24 for forming an insulation material by plug filling the cavities formed in the silicon monoxide and two-micron bottom photoresist layer; several insulation materials are available from which to choose, including calcium fluoride, silicon monoxide, yttrium oxide, and aluminum oxide, and the like.

28. The method of claim 24 for removing said bottom photoresist layer by lift-off with an ultrasonic bath, leaving the said alignment posts.

29. The method of claim 8 wherein said alignment posts are formed by the process of polyimide by photosensitive etching upon the OIL.

30. The method of claim 29 for forming a photosensitive polyimide layer of thickness between about 0.1 and 5

microns to achieve the desired height of the alignment posts.

31. The method of claim 29 for exposing the said photosensitive polyimide at the location of each planned alignment post.

32. The method of claim 29 for developing and removing the said photosensitive polyimide to leave the said alignment posts in the location of the exposed polyimide described herein, and removing the said photoresist mask.

33. A device structure that combines insulating materials for alignment posts associated with an active device structure in a silicon body.

34. A device structure that combines insulating materials for alignment posts and optical interference layers associated with an active device structure in a silicon body comprised of:

a silicon semiconductor wafer having a pattern of said active device structures therein and thereon;

pixels on said semiconductor wafer and the whole structure being covered with an optical interference layer;

bonding pads on the said silicon body having wire attached and said wire connected to external contacts for the control logic and power;

liquid crystal material located in the valleys below the peaks of the alignment posts;

glass cover placed upon and supported by the alignment posts to encapsulate the said liquid crystal material, but not over the area outside the liquid-crystal material where the bonding pads are located.

35. A structure according to Claim 34 wherein the alignment posts are made by means of photolithography rather than pre-formed glass beads or rods.

36. A structure according to Claim 34 that contains the said optical interference layers in addition to the said alignment posts.

ABSTRACT

Five new methods for the formation of an improved liquid-crystal-on-silicon display are described, in which the device structure is enhanced by the photolithographic building of alignment posts among the mirror pixels of the micro-display. These five methods accommodate the fabrication of an optical interference multilayer, which improves the image quality of the reflected light. These five methods are:

Silicon Dioxide Posts by Wet Etching.

Amorphous Silicon Posts by Plasma Etching.

Silicon Nitride Posts by Plug Filling.

Insulation Material Posts by Lift-off.

Polyimide Posts by Photosensitive Etching.

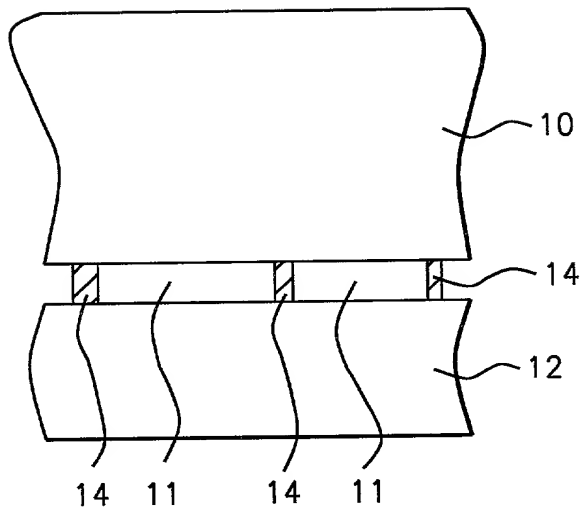


FIG. 1

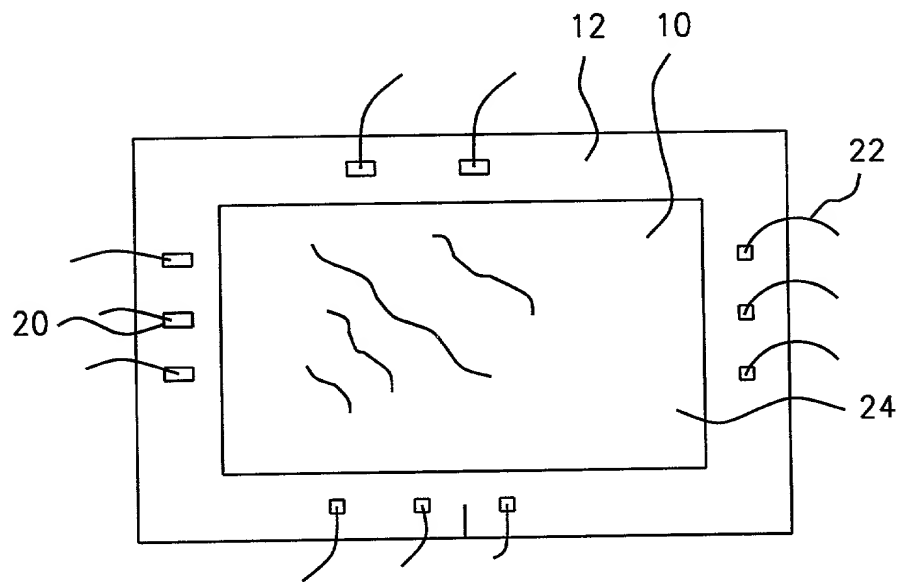


FIG. 2

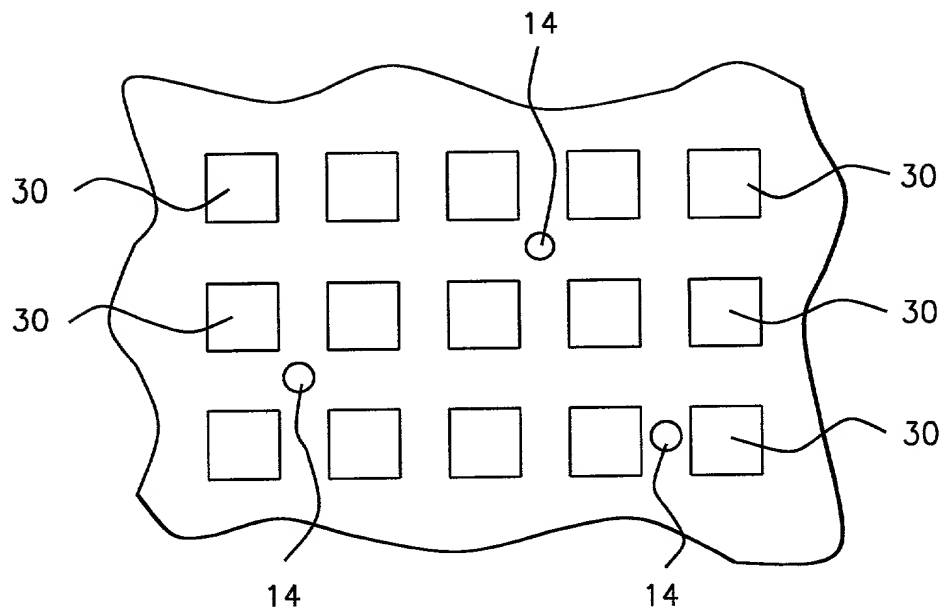


FIG. 3

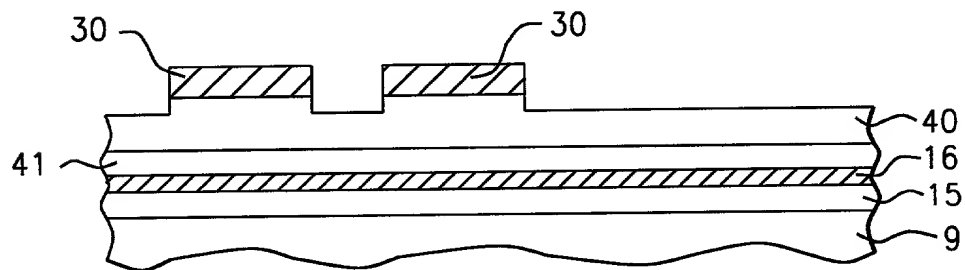


FIG. 4

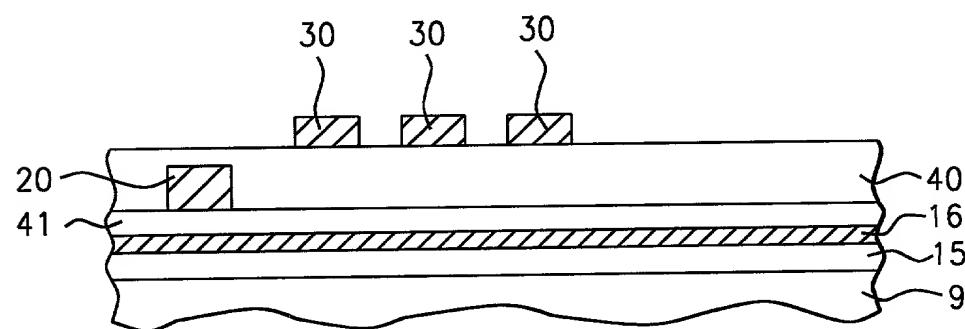


FIG. 5

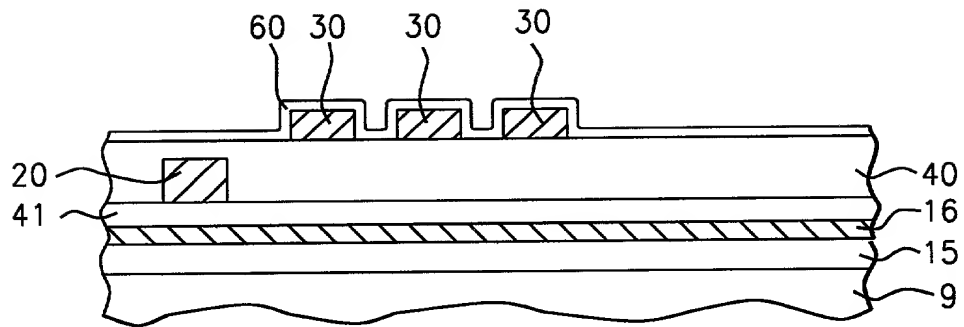


FIG. 6

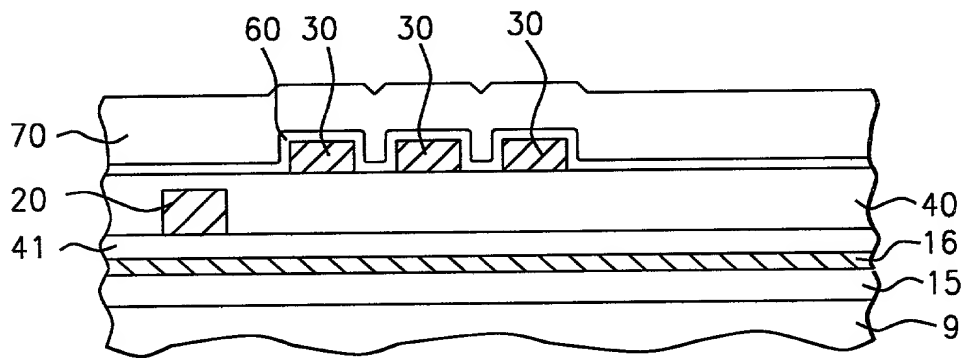


FIG. 7

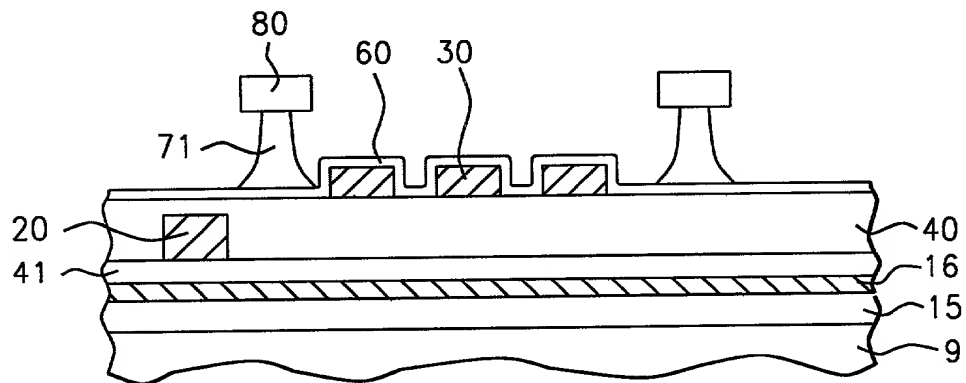
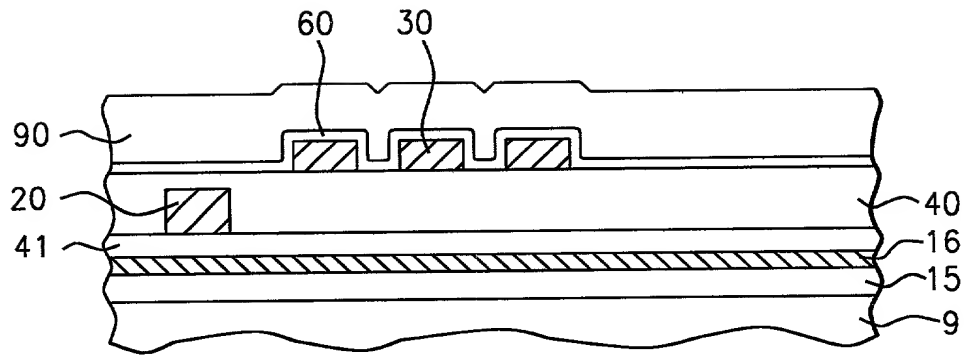
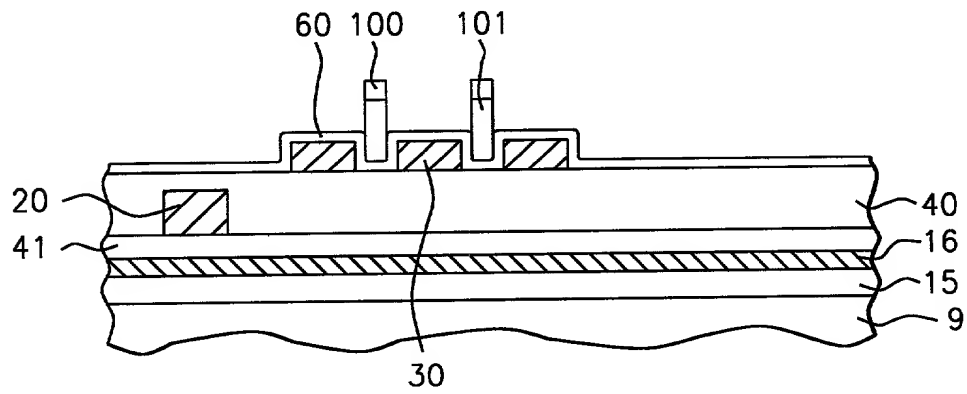
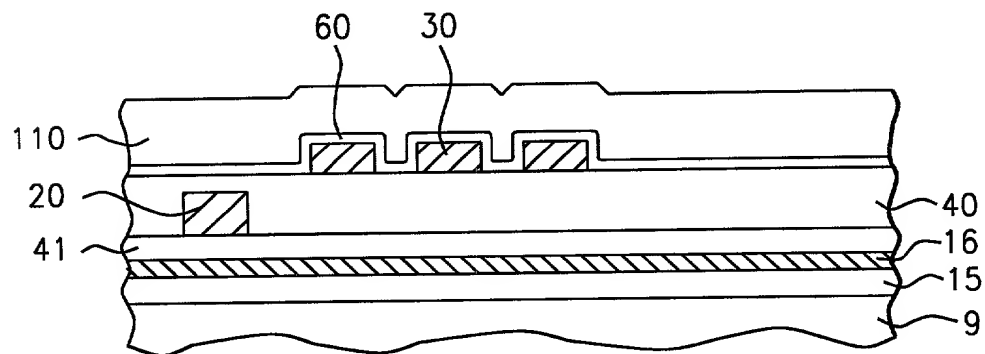


FIG. 8

*FIG. 9**FIG. 10**FIG. 11*

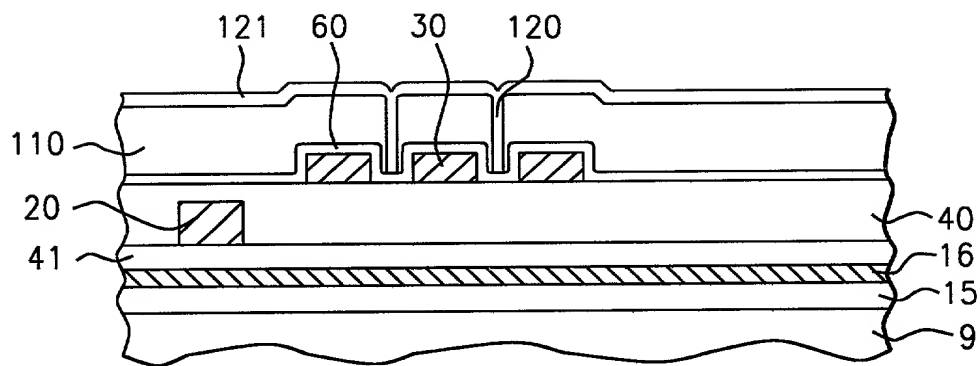


FIG. 12

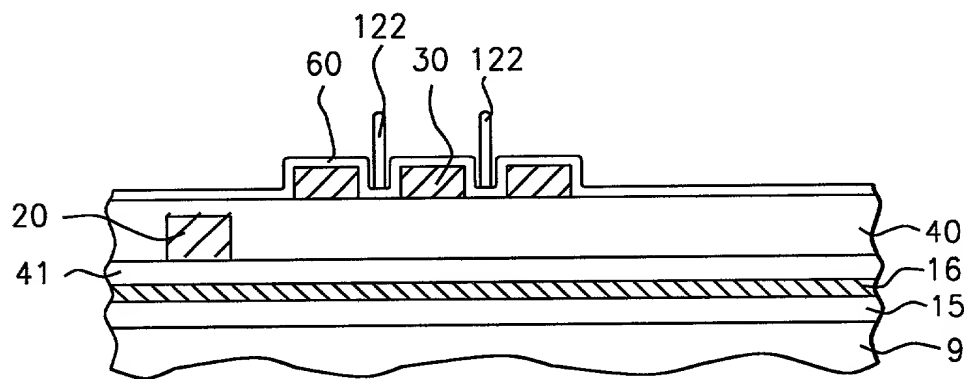


FIG. 13

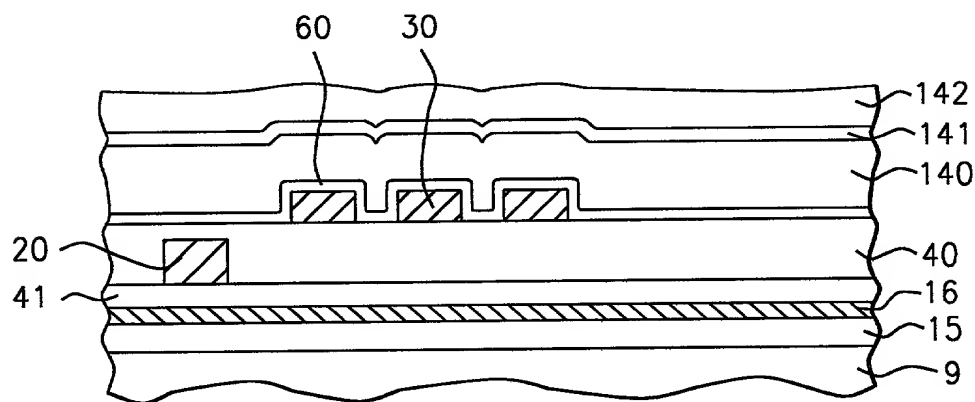


FIG. 14

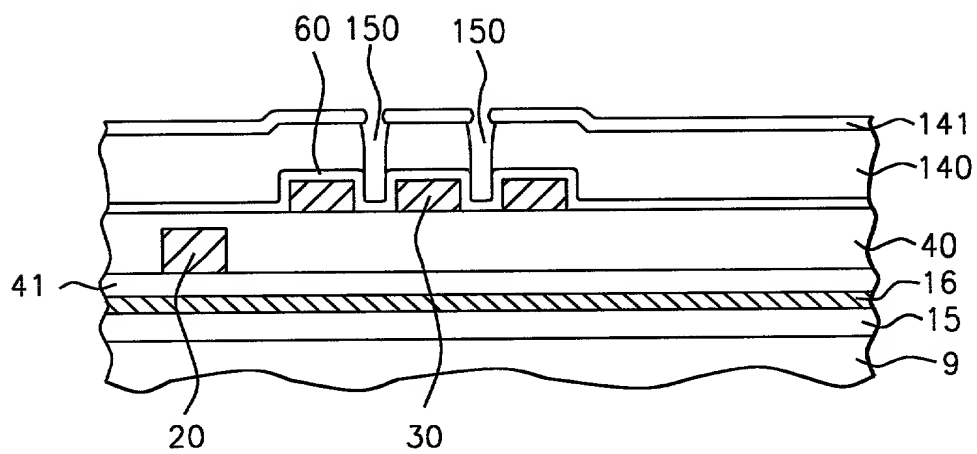


FIG. 15

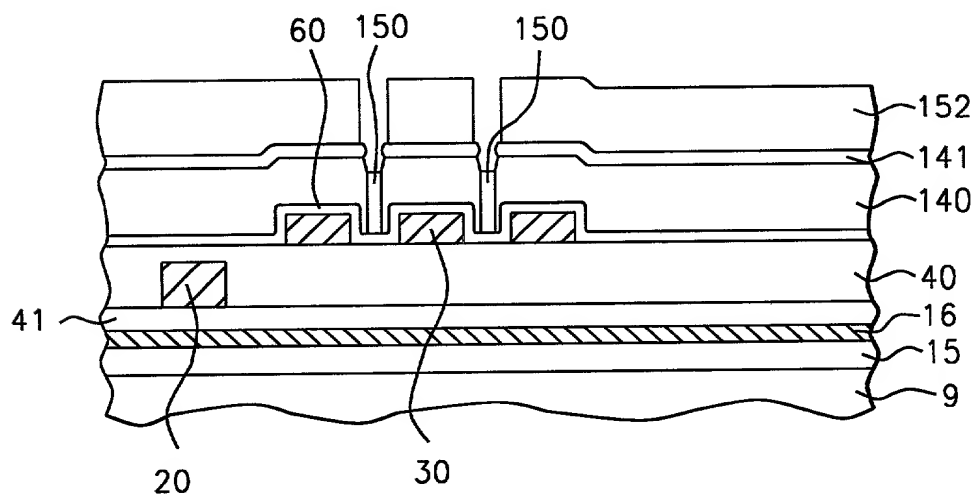
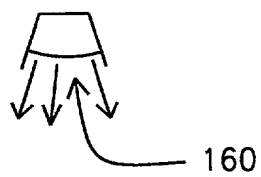


FIG. 16

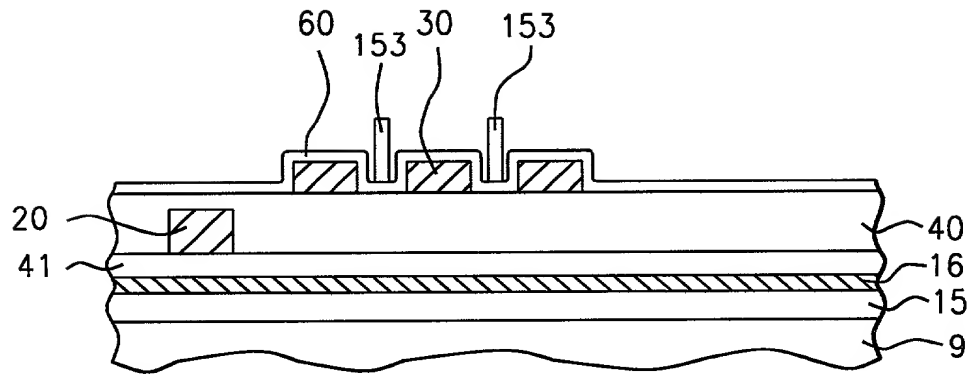


FIG. 17

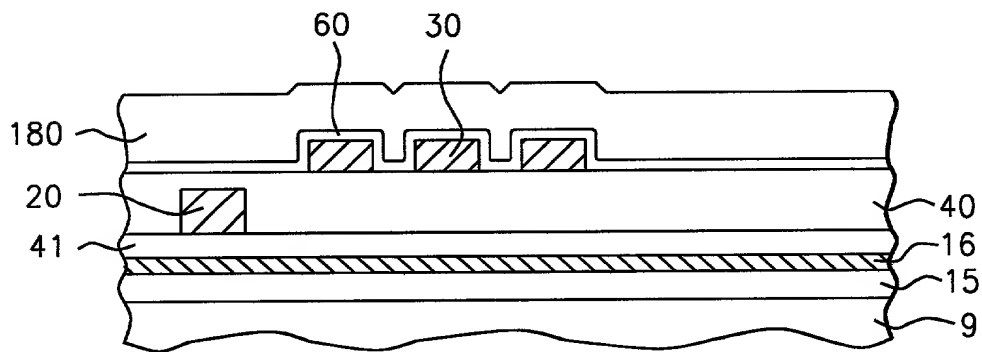


FIG. 18

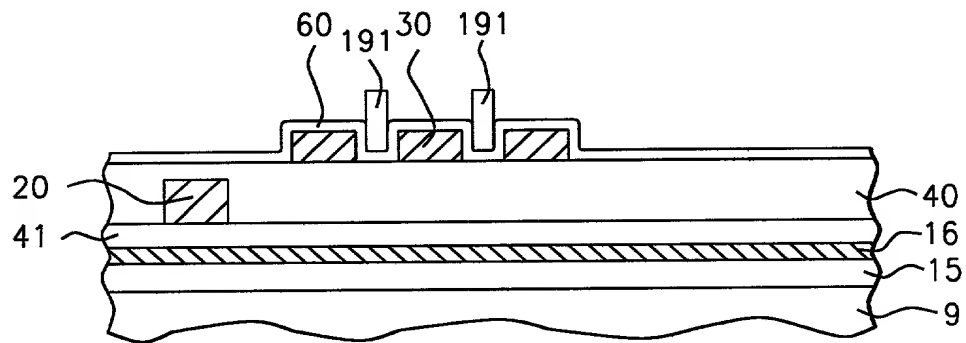


FIG. 19

2025 RELEASE UNDER E.O. 14176

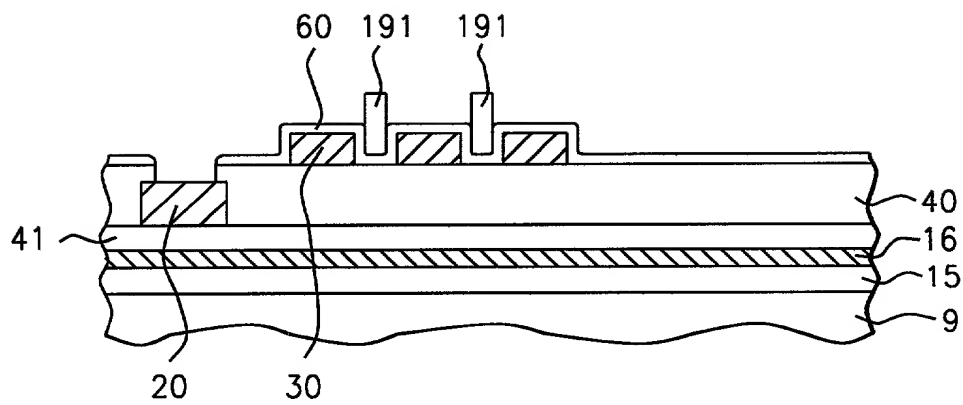


FIG. 20

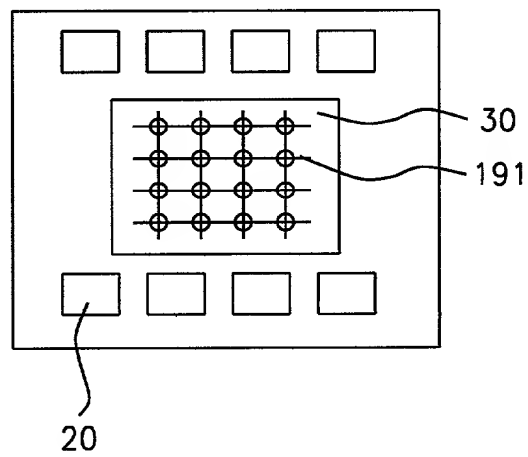
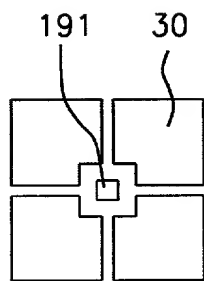


FIG. 21a

FIG. 21b

DECLARATION AND POWER OF ATTORNEY FOR PATENT APPLICATION

DOCKET NO. CS98-076

As a below named Inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name;

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled Photolithographic Methods For Making Liquid-Crystal-On-Silicon Displays With Alignment Posts And Optical Interference Layers

the specification of which (check one)

X is attached hereto.

was filed on _____

Application Serial No. _____

and was amended on _____ (if applicable)

I hereby state that I have reviewed and understand the contents of the above Identified specification including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose information which is material to the examination of this application in accordance with Title 37, Code of Federal Regulations, §1.56(a).

I hereby claim foreign priority benefits under Title 35, United States Code §119 of any foreign application(s) for patent or inventor's certificate listed below and have also identified below any foreign application for patent or inventor's certificate having a filing date before that of the application on which priority is claimed.

Prior Foreign Application(s)

Priority Claimed:

(Number)	(Country)	(Day/Month/Year Filed)
(Number)	(Country)	(Day/Month/Year Filed)

I hereby claim the benefit under Title 35, United States Code §120 of any United States application(s) listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of Title 35, United States Code, §112, I acknowledge the duty to disclose material information as defined in Title 37, Code of Federal Regulations, §1.56(a) which occurred between the filing date of the prior application and the national or PCT international filing date of this application:

(Application Serial No.)	(Filing Date)	(Status) (patented, pending, abandoned)
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I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

POWER OF ATTORNEY: As a named inventor, I hereby appoint the following attorney(s) and/or agent(s) to prosecute this application and transact all business in the Patent and Trademark Office connected therewith. (list name & registration no.)

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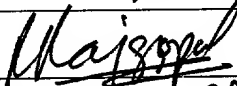
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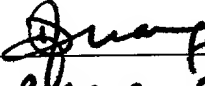
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